



# Silicon Photomultiplier Technologies Developed at Fondazione Bruno Kessler

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Detector-grade clean-room, 6 inches, class 10 and 100



Silicon Photomultipliers account for a significant portion of the detectors fabricated here.

Publicly funded research center

450 researches working in different fields

FBK is typically interested in R&D activities, and collaborations.  
Industrialization is carried out relying on partners.



**LFOUNDRY**  
Solutions  
for great visions

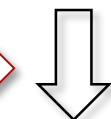


**BROADCOM**<sup>®</sup>

# FBK SiPM technology roadmap

Original technology 2005

**Electric field engineering**

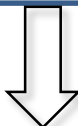


**RGB**  
**NUV**

2010

2012

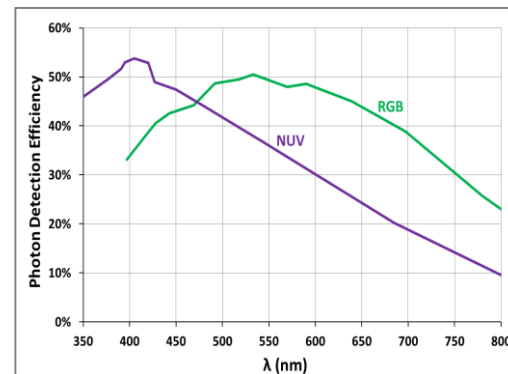
**New cell border (trenches)**



**RGB-HD**  
**NUV-HD**

2012

2015



*Ongoing Developments*

**NUV-HD-Cryo**

**VUV-HD**

**RGB-UHD**

**NIR**

# Near-UV technology: NUV-HD

Original technology 2005

*Electric field  
engineering*

RGB  
NUV

2010

2012

*New cell border  
(trenches)*

RGB-HD  
**NUV-HD**

2012

2015

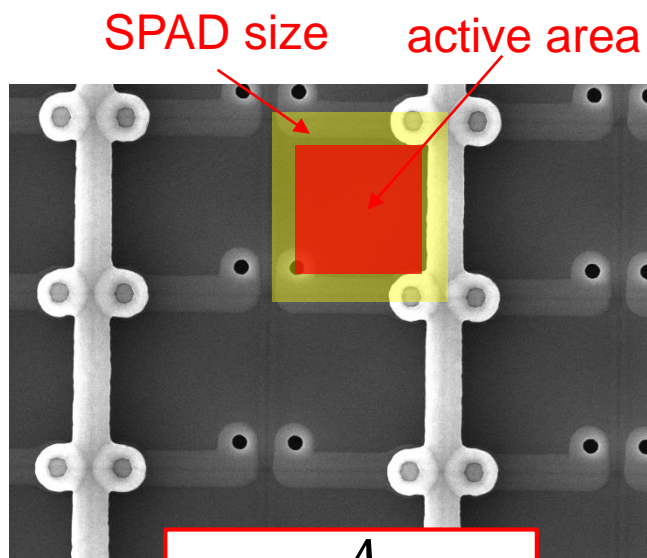
NUV-HD-Cryo

VUV-HD

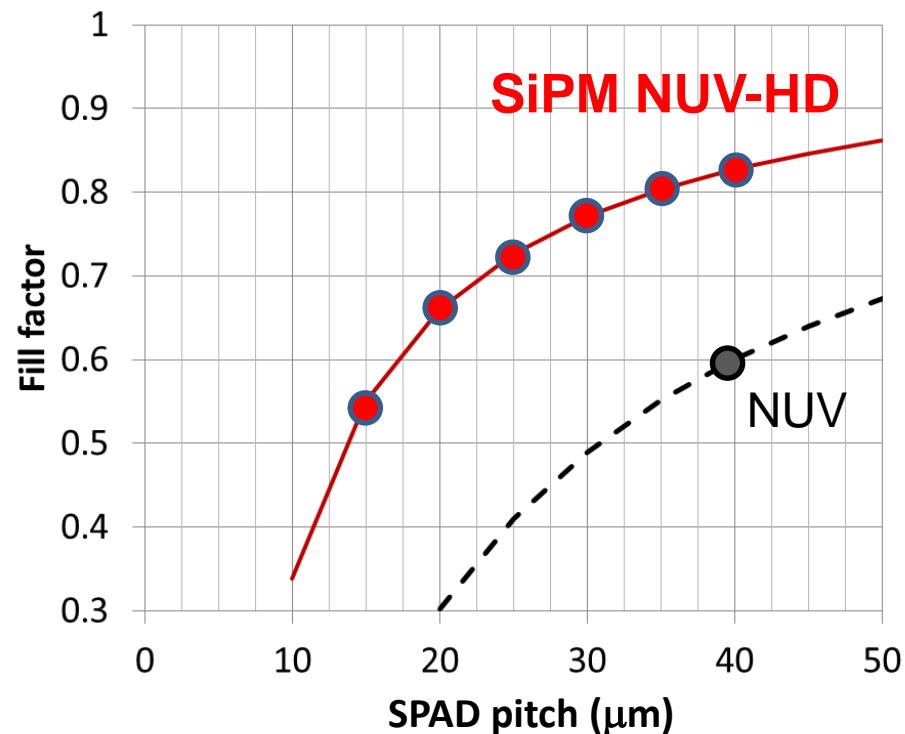
RGB-UHD

NIR

# NUV-HD: Fill Factor



$$FF = \frac{A_{active}}{A_{total}}$$



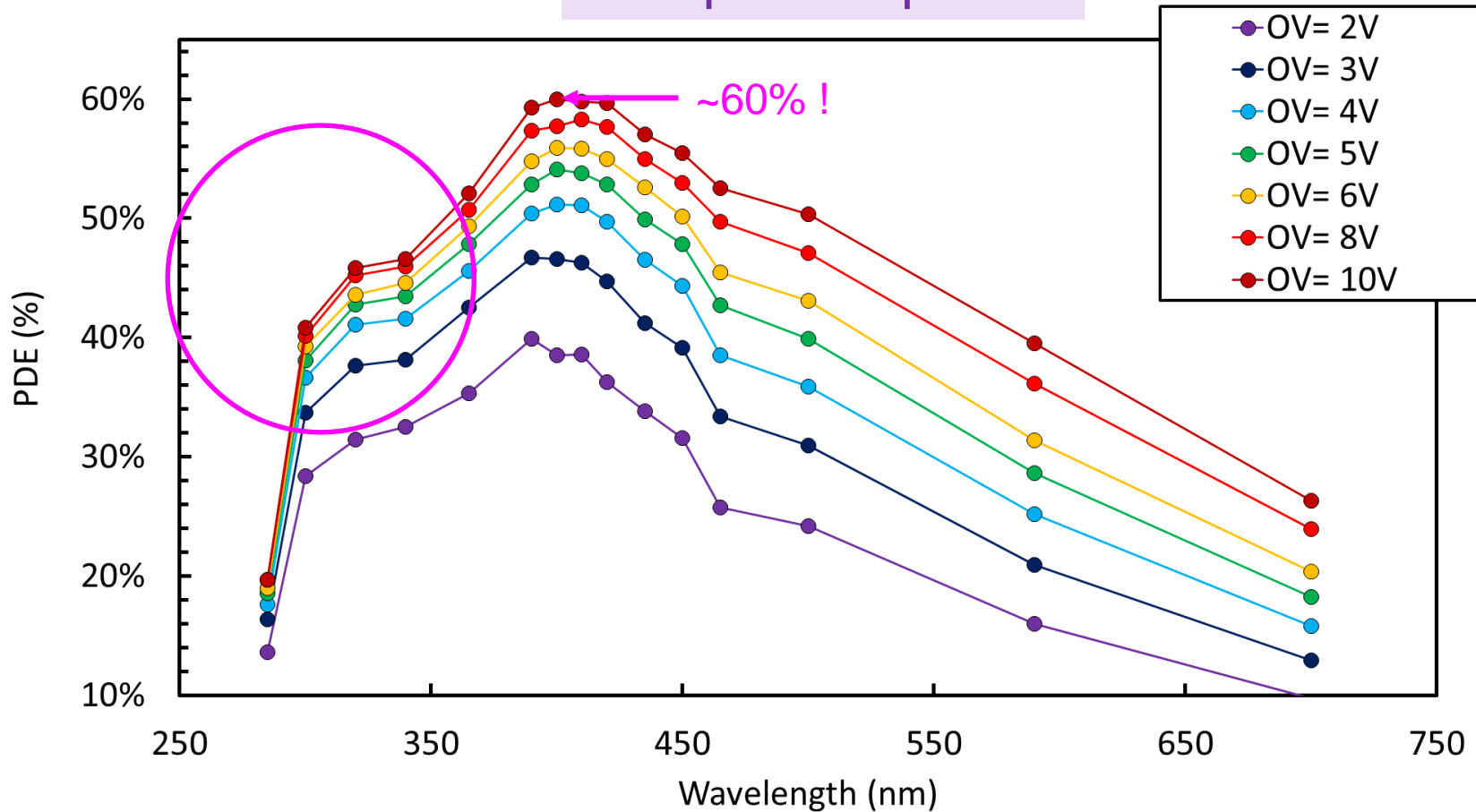
SPAD Pitch	15 $\mu\text{m}$	20 $\mu\text{m}$	25 $\mu\text{m}$	30 $\mu\text{m}$	35 $\mu\text{m}$	40 $\mu\text{m}$
Fill Factor (%)	55	66	73	77	81	83
SPAD/mm <sup>2</sup>	4444	2500	1600	1111	816	625

High Dynamic Range, Fast recovery time

High PDE

# Photon detection efficiency

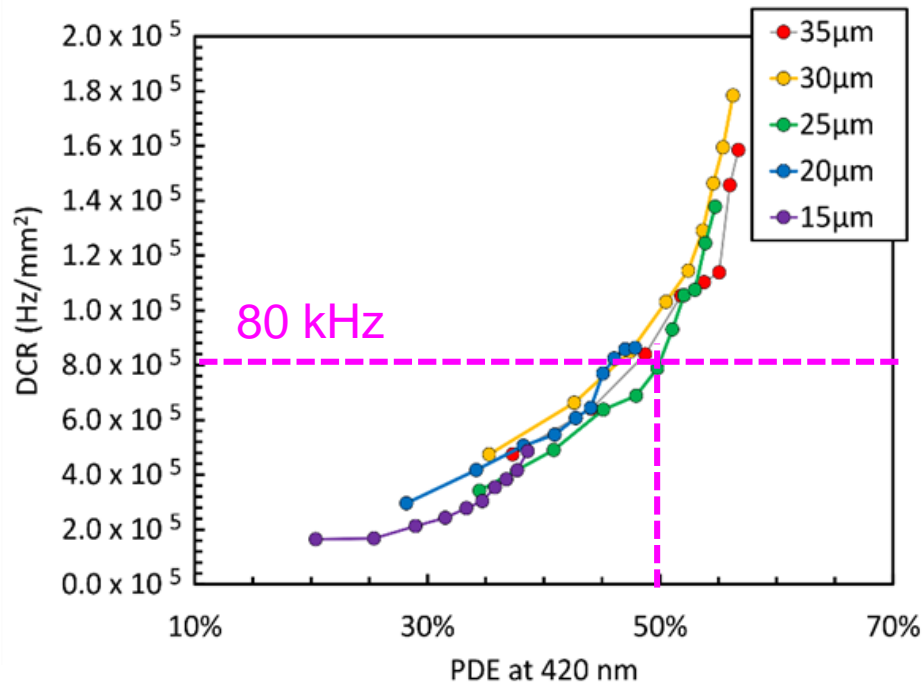
35  $\mu\text{m}$  cell pitch



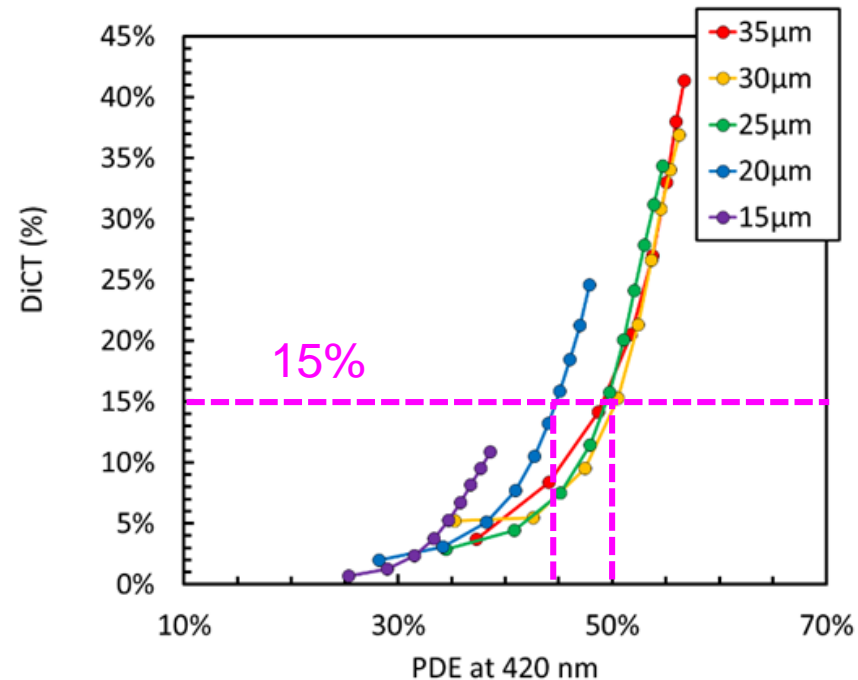
Gola, A et al. (2019). "NUV-Sensitive Silicon Photomultiplier Technologies Developed at Fondazione Bruno Kessler." *Sensors*, 19(2), 308.

# SiPM noise: Dark Count Rate and Optical Crosstalk

T = 20 C



Dark Count Rate



Optical Crosstalk  
(Correlated Noise)

# NUV-HD Improvements

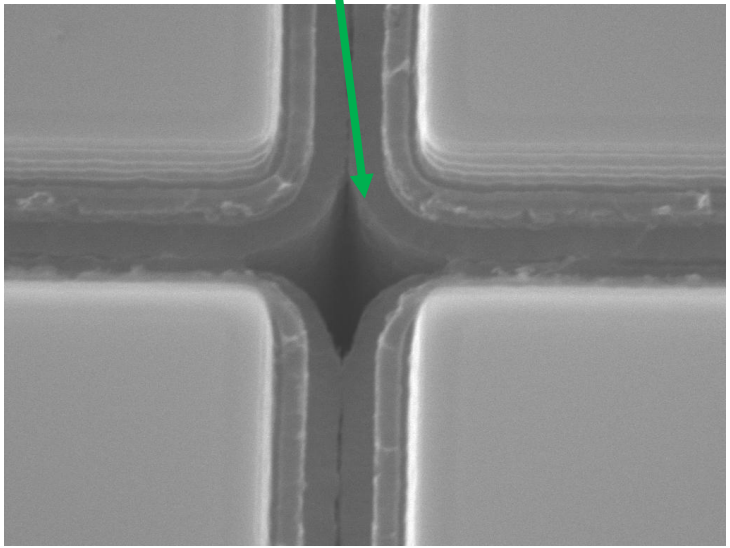


# NUV-HD-LowCT



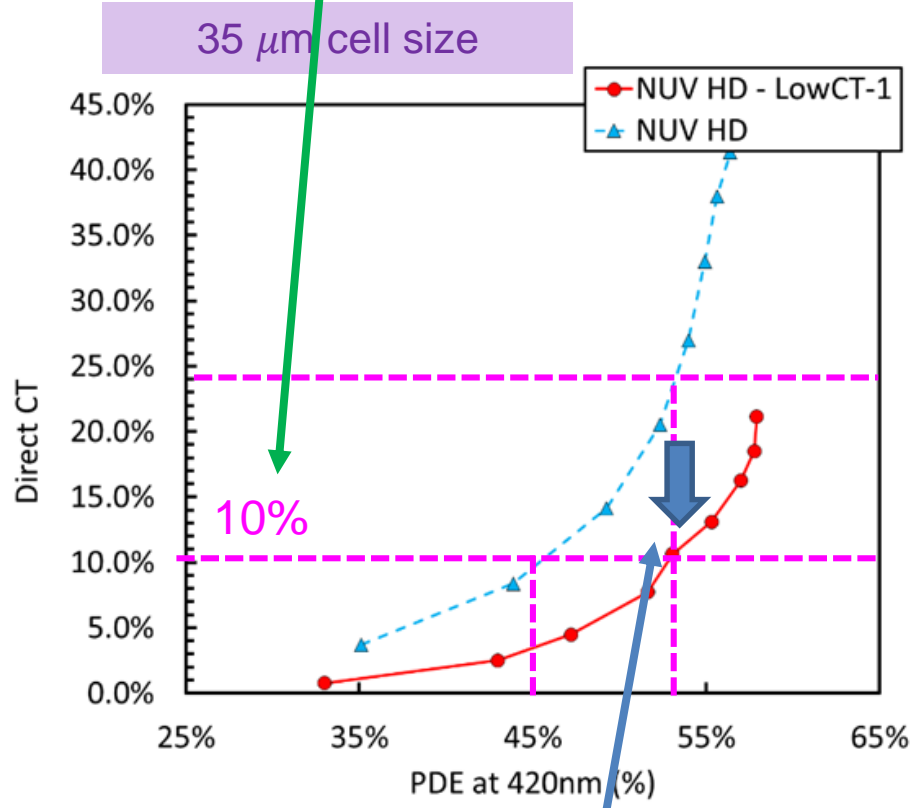
Applications such as CTA

Light absorbing material was inserted inside trenches, between adjacent microcells



SEM image of trenches, separating adjacent microcells.

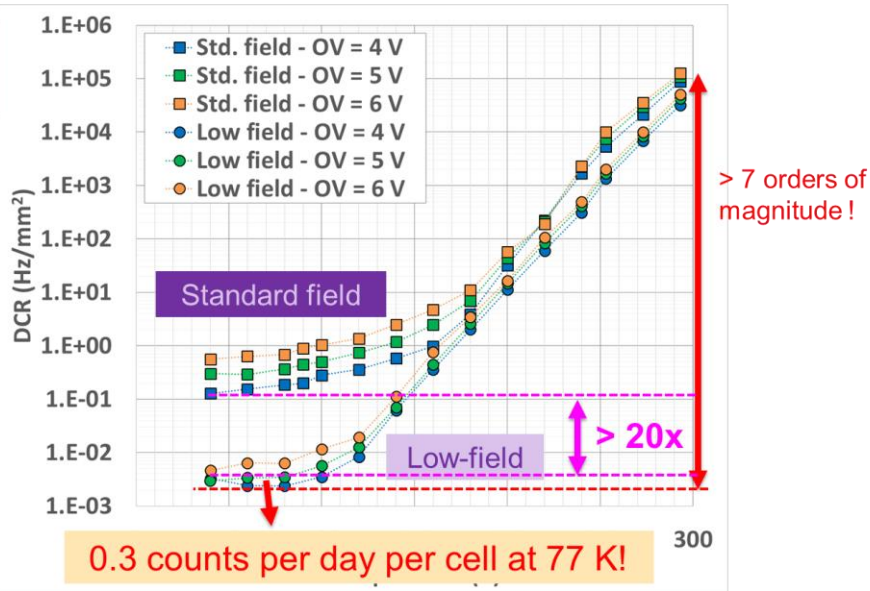
Metal in trenches is under development..



2.5x reduction of Optical Crosstalk at same PDE

# NUV-HD-Cryo and VUV-HD

25  $\mu\text{m}$   
cell



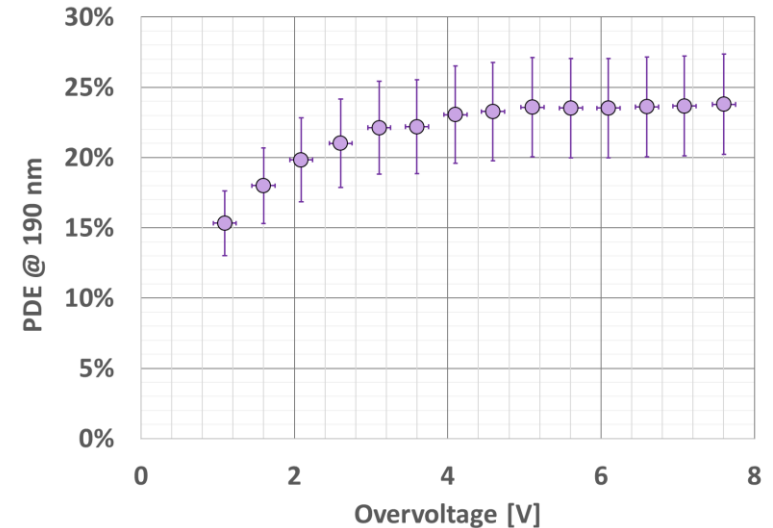
A 10x10 cm<sup>2</sup> SiPM array would have a total DCR < 100 cps!



See A. Razeto and I. Kochanek presentations



PDE vs OV  
(~190nm)



See F. Retière and M. Capasso presentations

# Radiation Damage of SiPMs

Radiation damage in SiPMs is currently a hot research topic in the SiPM field.

- Small-cell SiPMs fabricated at FBK (< 20 um cell size) with optimized electric field provide mitigation of typical effects of radiation damage.

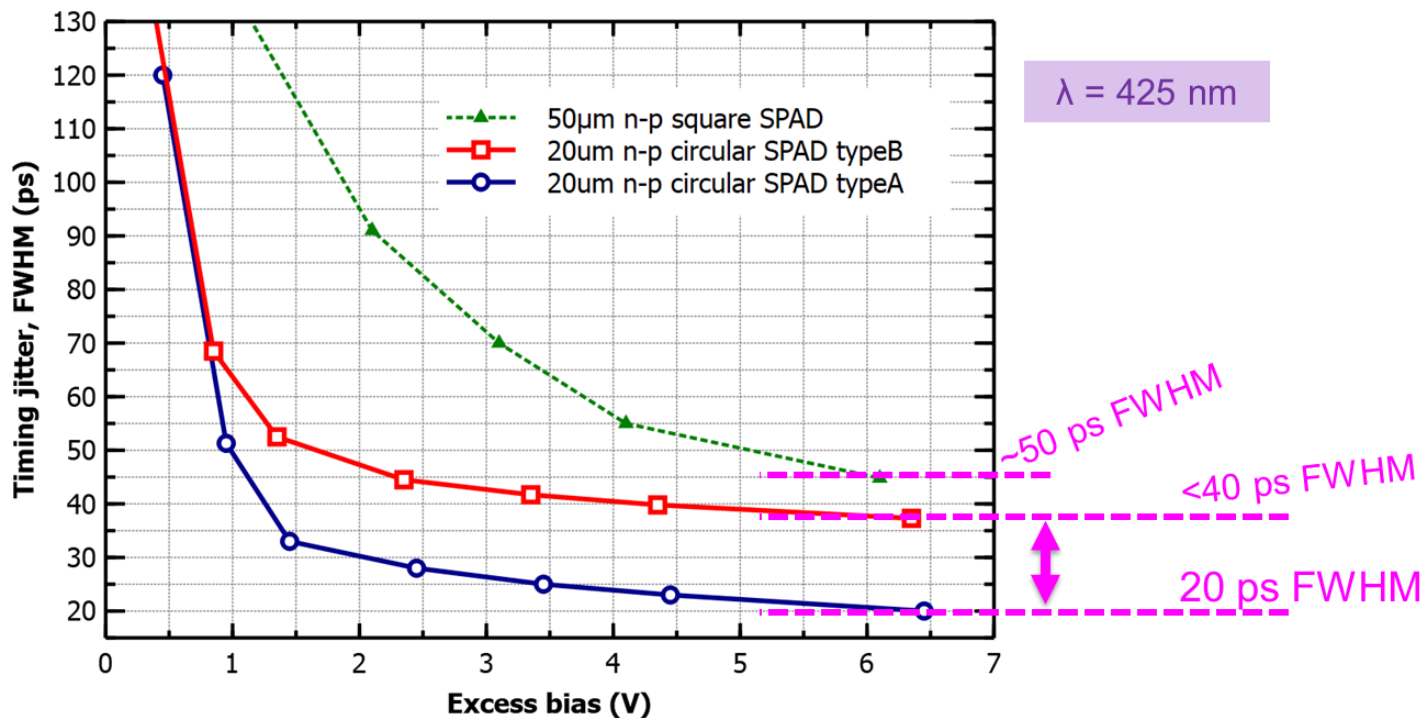
Main effects of radiation damage in SiPMs	Mitigation of the effects of rad. damage with HD-SiPM technology:
Increase of the <b>primary noise (DCR)</b> .	E field engineering allows a <b>faster reduction of DCR with cooling</b> .
Increased <b>afterpulsing</b> (increased number of traps).	<b>Low gain and low E field</b> reduce afterpulsing (for a given number of traps).
<b>PDE loss</b> due to cells busy triggering dark counts.	<b>Many, smaller cells with faster recharge</b> are less sensitive to the problem.
Increased <b>power consumption</b> due to higher DCR.	<b>Lower gain</b> allows less current (for a given value of DCR) + Low $V_{BD}$ .

# NUV-HD-LF with small cells

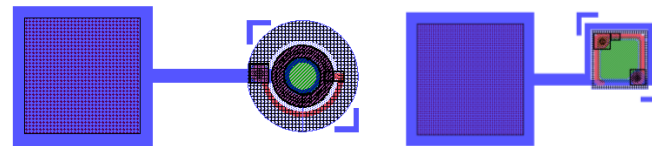


# Single Photon Time Resolution

# NUV SPAD – SPTR



ACTIVE AREA LAYOUT	Diameter / side ( $\mu\text{m}$ )	Metallization
circular	20	Covered edges (A) with metal
circular	20	uncovered edges (B)
square	50	uncovered edges



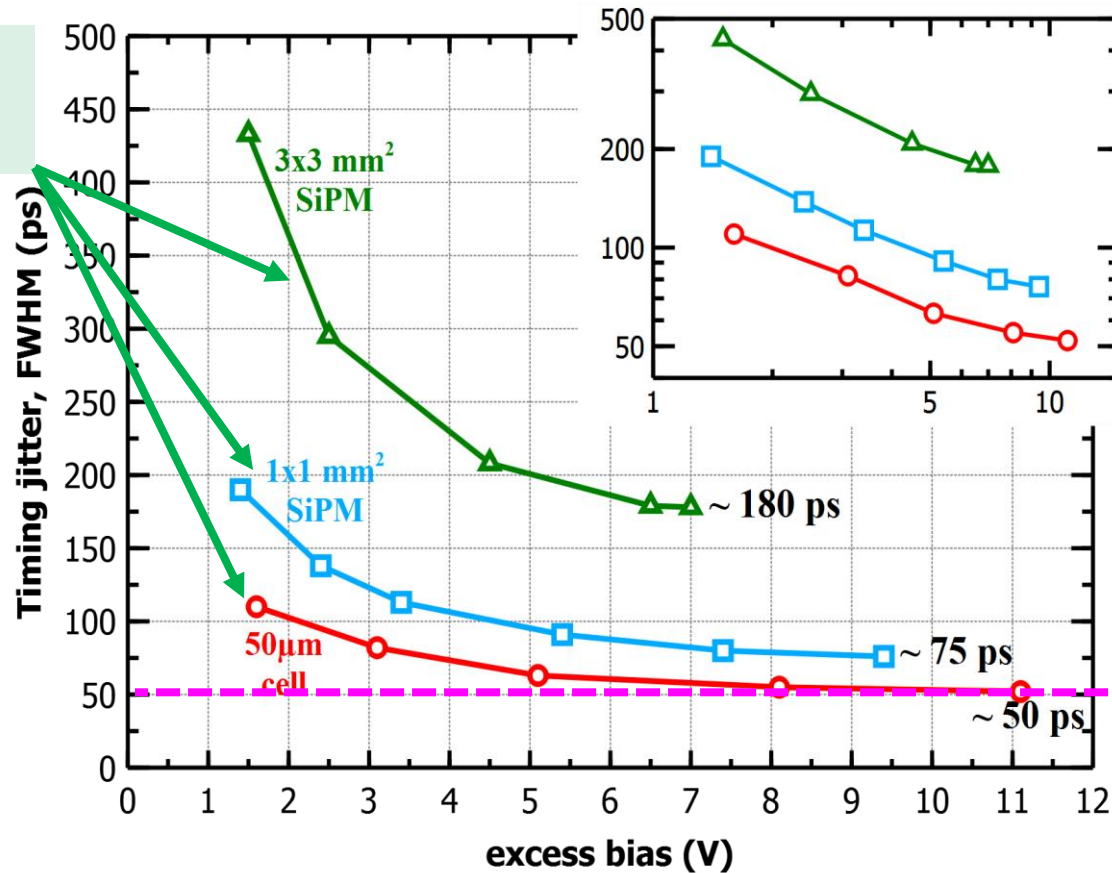
- 1) Worse charge collection at SPAD edges
- 2) Signal pick-up is also very important



Covering the SPAD edges with metal reduces the SPTR to 20 ps

# NUV SiPM – SPTR

Different  
SiPM sizes



$\lambda = 425 \text{ nm}$

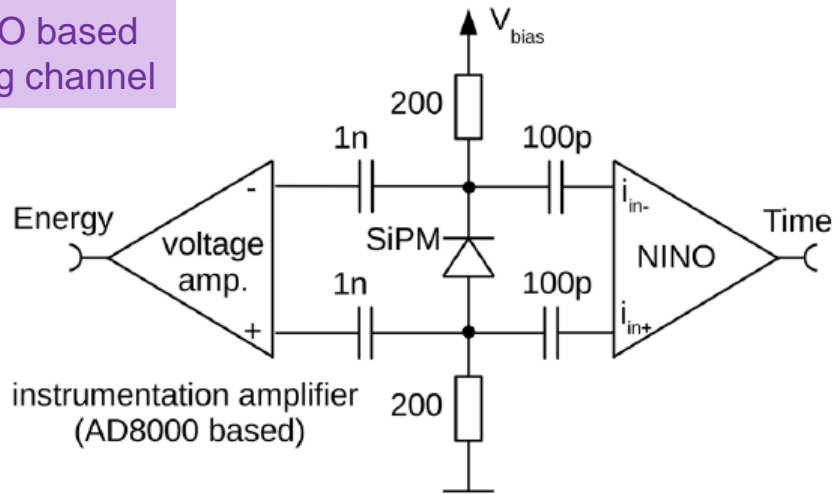
Larger active area  $\rightarrow$  larger SiPM capacitance  $\rightarrow$  more LP filtering  $\rightarrow$  smaller signal



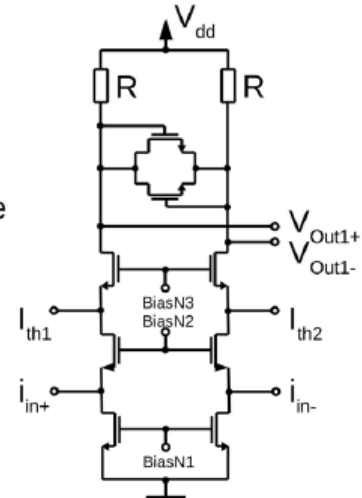
Bigger effect of the electronic noise on SPTR

# High-frequency SiPM readout

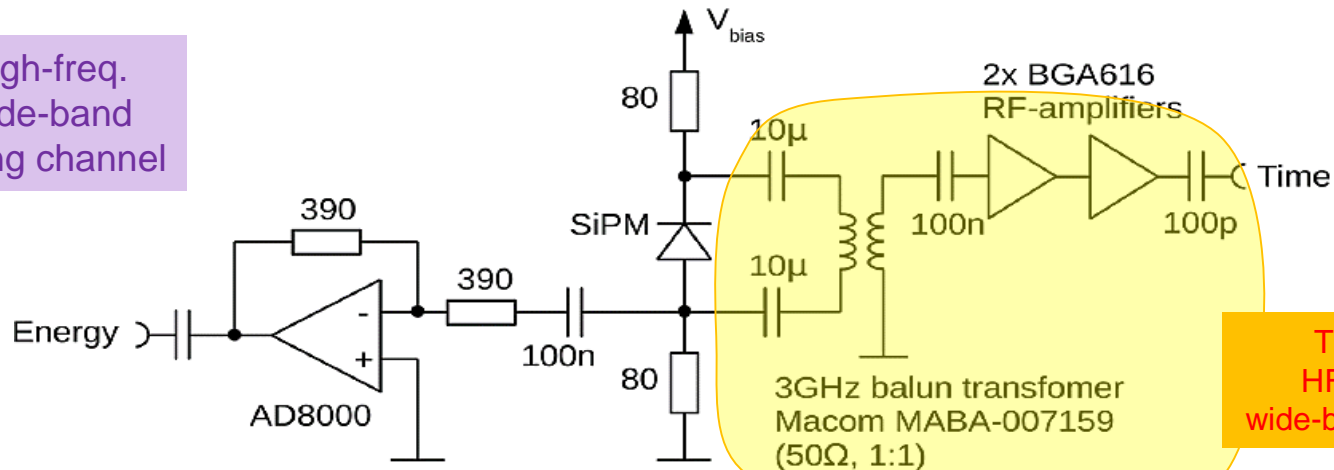
NINO based  
timing channel



NINO input stage:



High-freq.  
wide-band  
timing channel



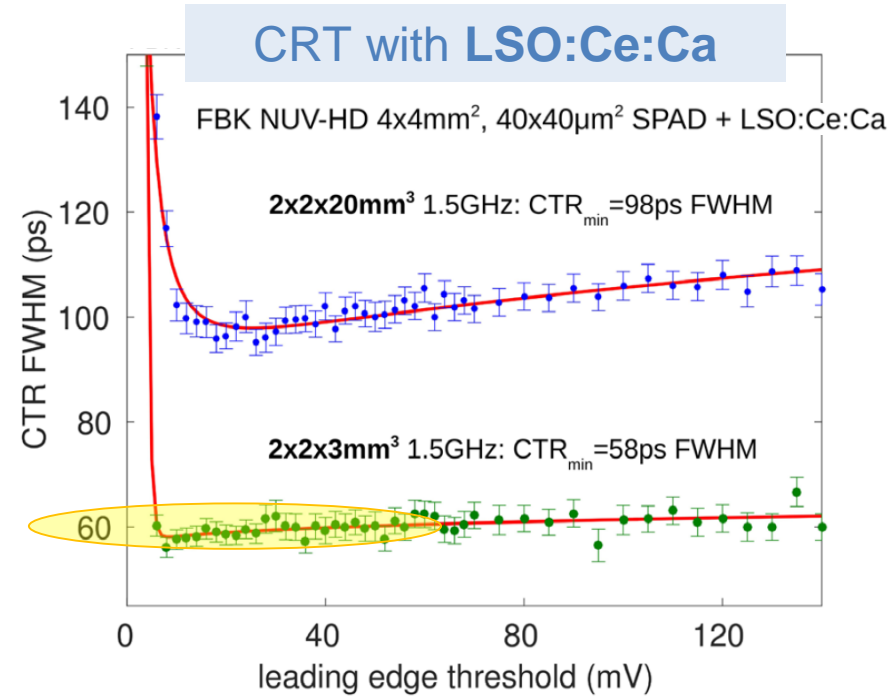
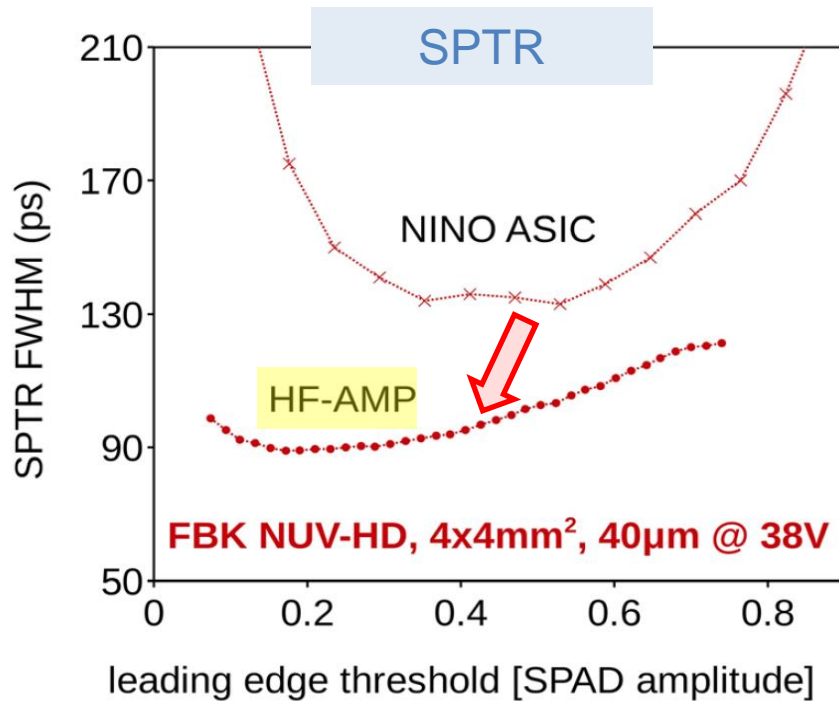
Timing signal:  
HF readout and  
wide-band amplification



S Gundacker et al, "High-frequency SiPM readout advances measured coincidence time resolution limits in TOF-PET"

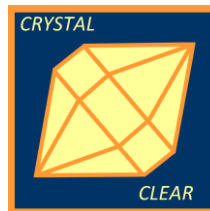
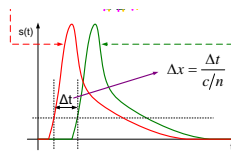
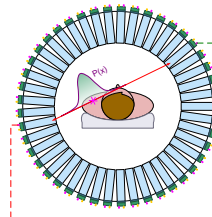


# HF SiPM readout – SPTR and CRT with LSO

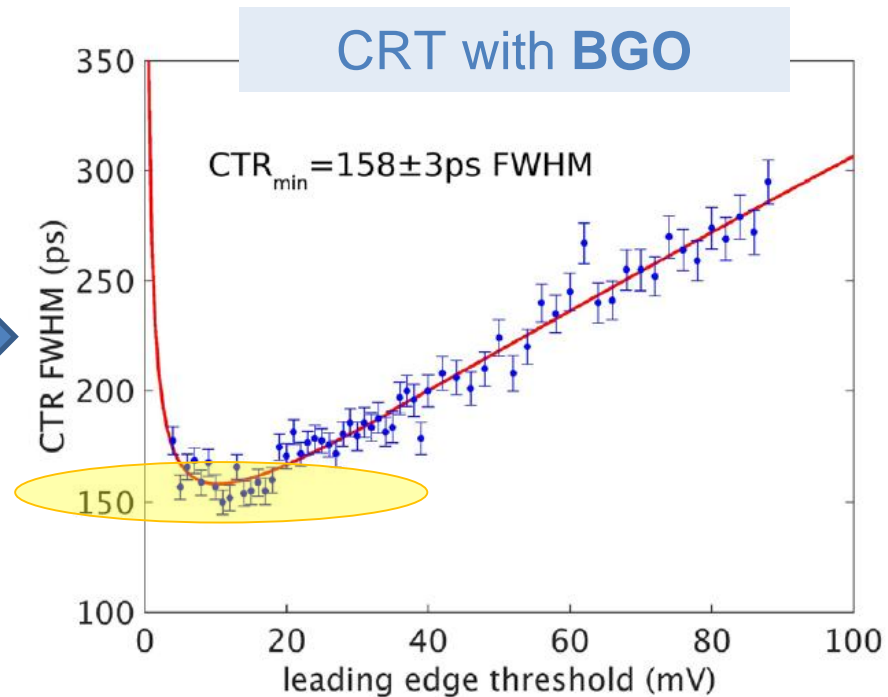
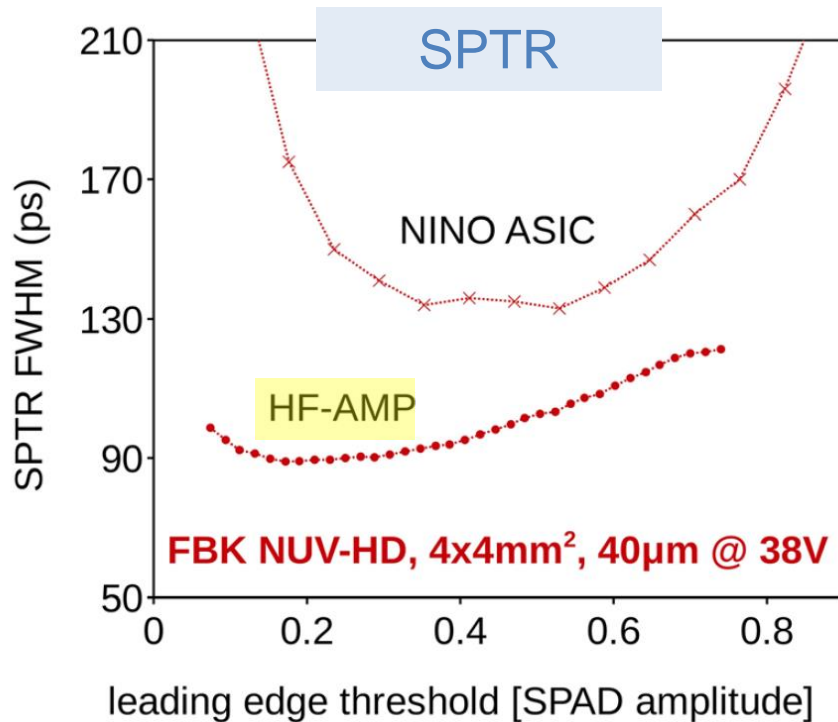


Significant reduction of SPTR with improved electronics (but high power consumption)

Work carried out in collaboration with S. Gundacker (P. Lecoq)

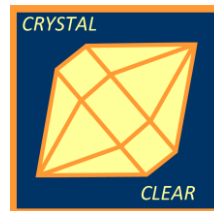


# HF SiPM readout – SPTR and CRT with BGO



Improvement of SPTR is, possibly, even more important for BGO readout:

- Timing is improved with Cherenkov light detection



# RGB-HD technology

Original technology 2005

*Electric field engineering*

RGB  
NUV

2010

2012

*New cell border (trenches)*

**RGB-HD**  
NUV-HD

2012

2015

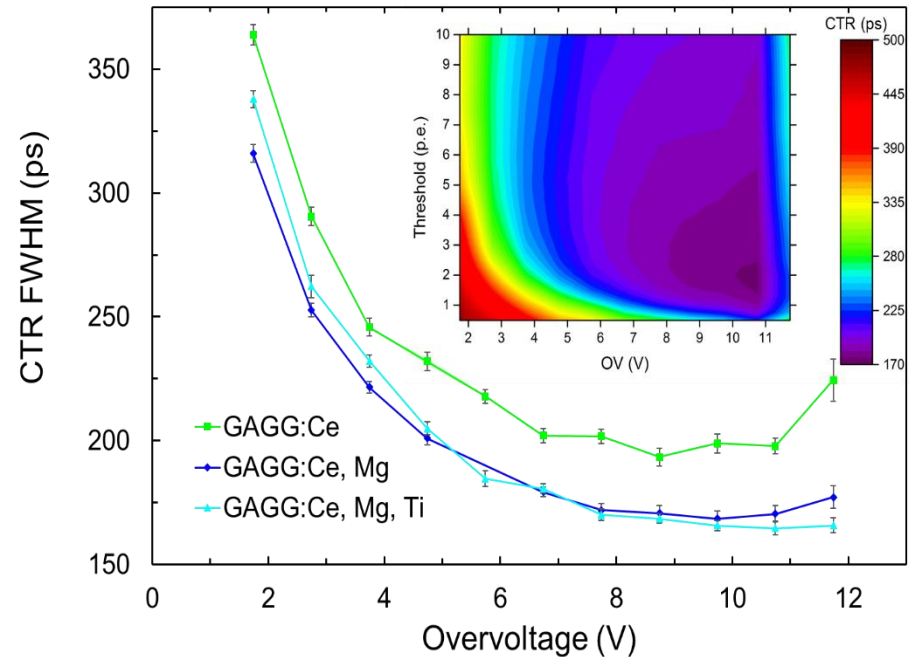
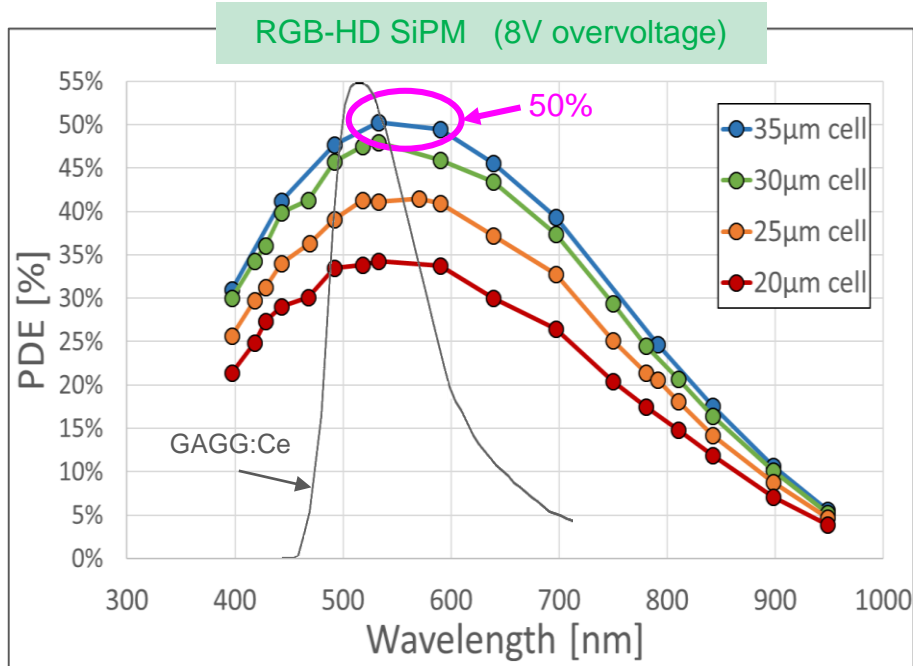
NUV-HD-Cryo

VUV-HD

RGB-UHD

NIR

# Timing with RGB-HD SiPMs coupled to GAGG



Tumulatis, et. al., "Improvement of response time in GAGG:Ce scintillation crystals by magnesium Codoping" DOI: 10.1063/1.5064434

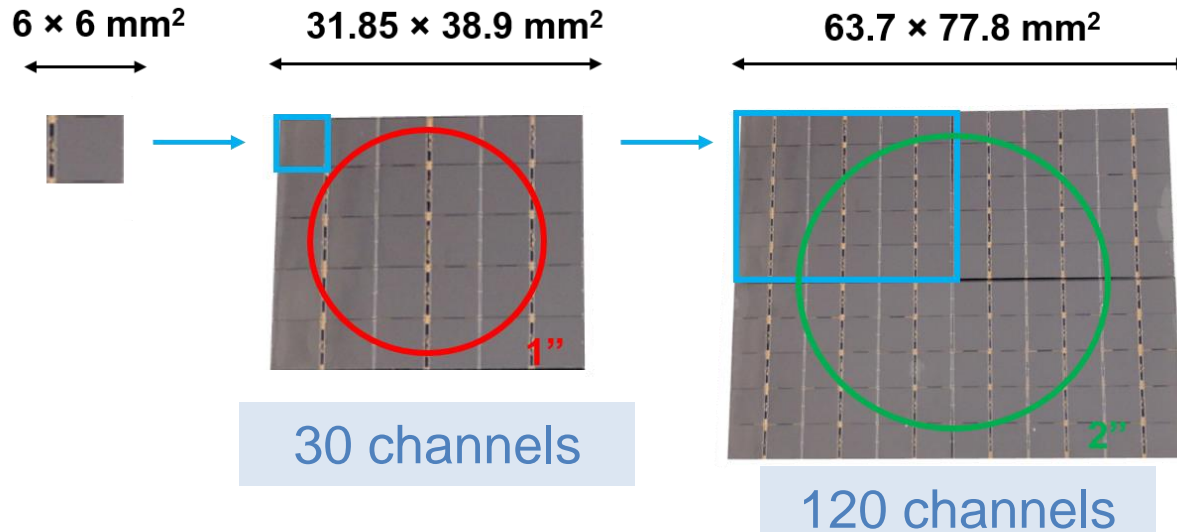
- RGB-HD technology: optimized for green wavelength detection
- Good for CsI and GAGG scintillators



CTR with GAGG: Ce, Mg, Ti:  
~170ps FWHM

# Gamma-ray spectroscopy with NUV-HD SiPMs

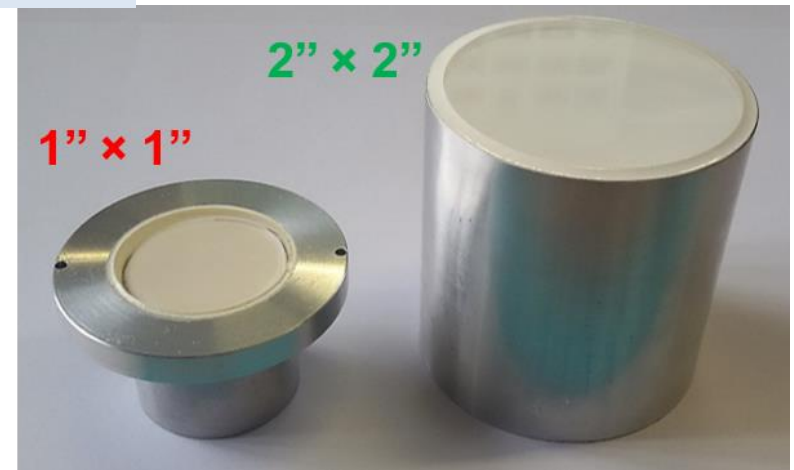
# LaBr<sub>3</sub> readout by SiPMs



New prototype of 3x3 arrays with 4x4 SiPMs was developed for the readout of 3" × 3" LaBr<sub>3</sub>:Ce crystal.

SiPM: basic unit is NUV-HD SiPM (FBK)

- 6 × 6 mm<sup>2</sup> active area
- 30 × 30 μm<sup>2</sup> microcells
- Peak efficiency of 45% at 380 nm
- DCR < 100 kcps/mm<sup>2</sup>
- ASIC readout



LaBr<sub>3</sub> crystals

# LaBr<sub>3</sub> spectroscopy results



3'' LaBr<sub>3</sub>:Ce

3'' LaBr<sub>3</sub>:Ce,Sr<sup>2+</sup>

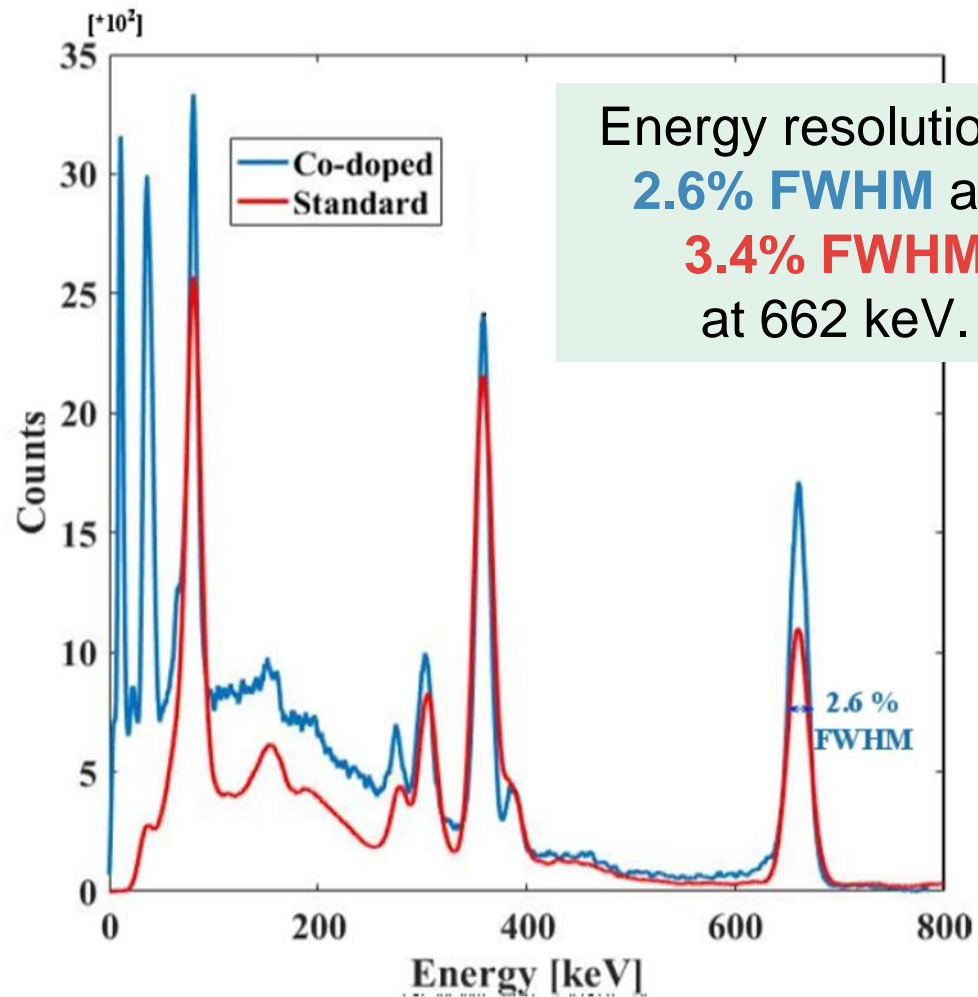
Multi-source

(<sup>133</sup>Ba and <sup>137</sup>Cs sources)

No collimator

Measured at

Politecnico di Milano



Montagnani et al., 2019, **Spectroscopic performance of a Sr co-doped 3'' LaBr<sub>3</sub> scintillator read by a SiPM array**, Nuclear Instruments and Methods in Physics Research Section A

# Thank you!

For any question:  
[gola@fbk.eu](mailto:gola@fbk.eu)

Thanks also to all the members of the team working on custom SiPM technology at FBK:

Fabio Acerbi  
Anna Rita Altamura  
Giacomo Borghi  
Massimo Capasso  
Andrea Ficarella  
Nicola Furlan  
Alberto Mazzi  
Stefano Merzi  
Vladimir Mozharov  
Giovanni Paternoster  
Veronica Regazzoni  
Nicola Zorzi



# Linearly-Graded SiPM

## LG-SiPM

# Linearly-Graded SiPM – LG-SiPM

Original technology 2005

*Electric field  
engineering*

RGB  
NUV

2010

2012

*New cell border  
(trenches)*

**RGB-HD**  
NUV-HD

2012

2015

LG-SiM is a new  
SiPM type  
built in  
RGB-HD  
technology

NUV-HD-LF

VUV-HD

RGB-UHD

NIR

# LG-SiPM

- Linearly-Graded Silicon Photomultiplier
  - A type of position-sensitive silicon photomultipliers (PS-SiPM).
  - 4 cathode signals (position information) and 1 anode signal.
- The currents of the 4 cathode signals change **linearly** according to the position of the fired microcell.

- Position

$$x = \frac{L - R}{L + R} \quad y = \frac{T - B}{T + B}$$

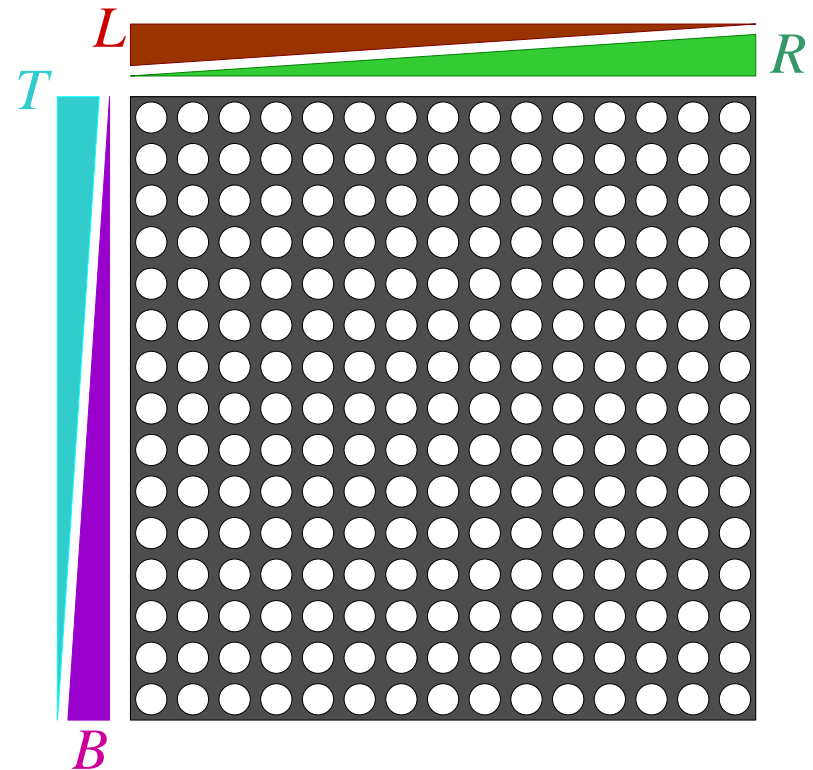
- Energy

$$E = L + R + T + B$$

Several microcells triggered

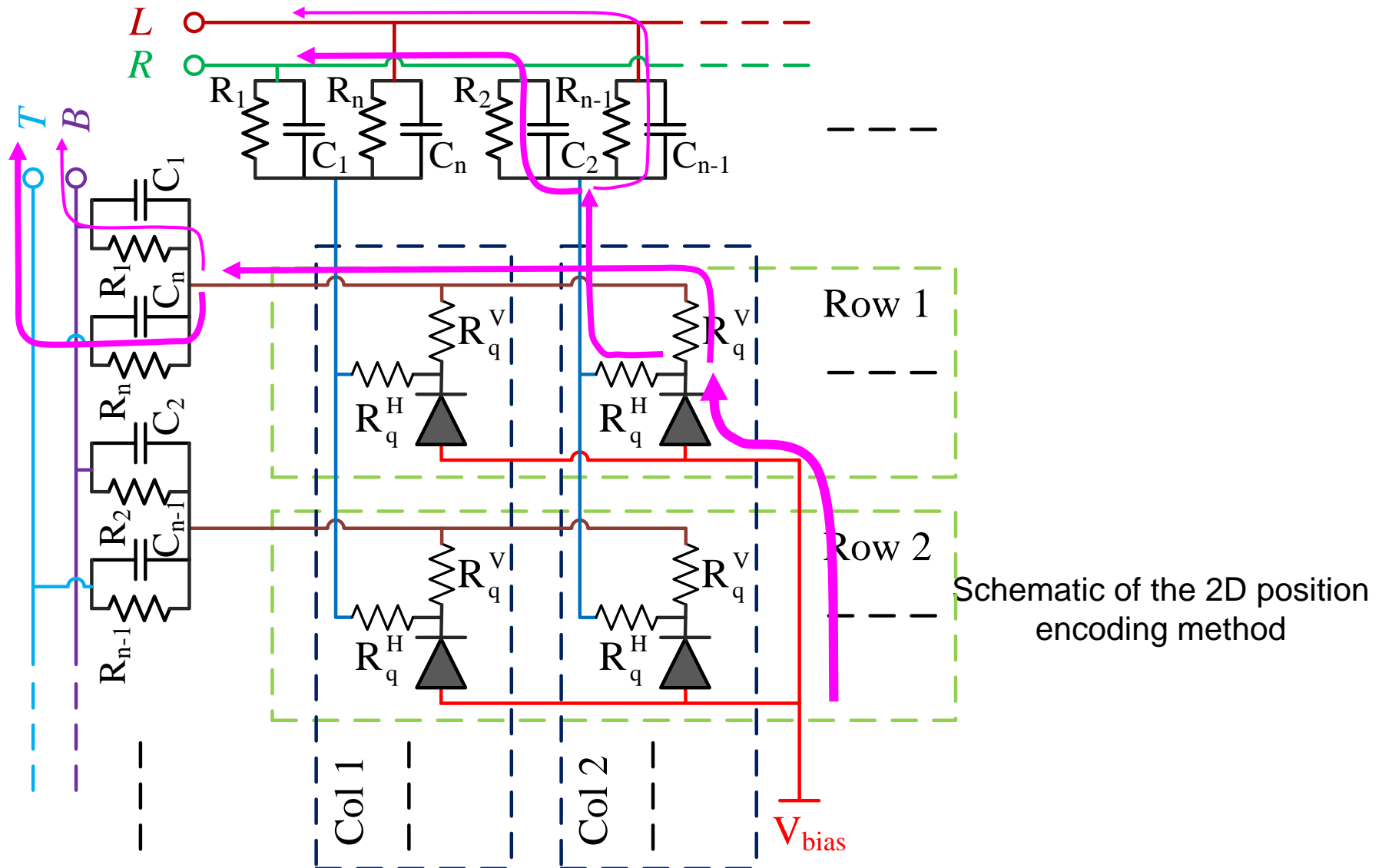


Implements the Center  
of Gravity



Basic idea of the LG-SiPM.

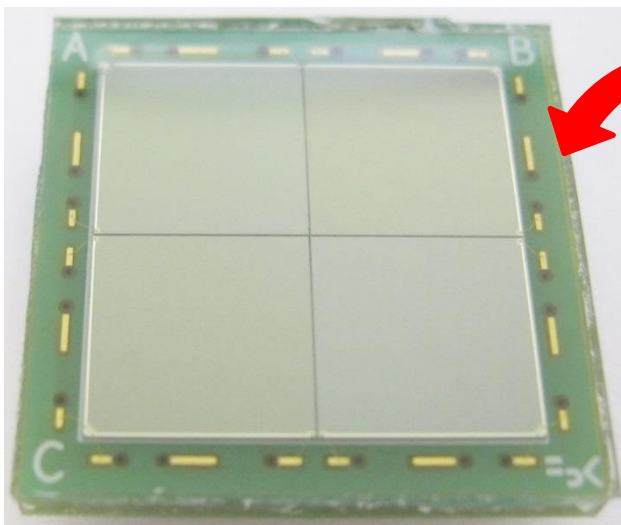
# LG-SiPM



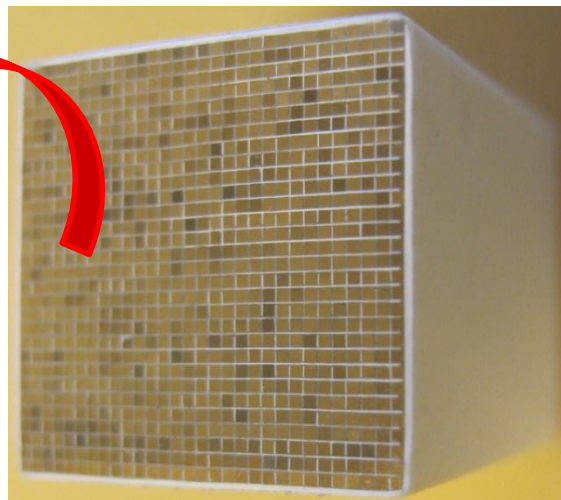
# 2 x 2 array of LG-SiPMs

- 2 x 2 array of 7.75 x 7.75 mm<sup>2</sup> LG-SiPMs
- Microcell size: 20 μm (square cells).
- Gap between LG-SiPMs is 0.2 mm.
- Application: small-animal PET

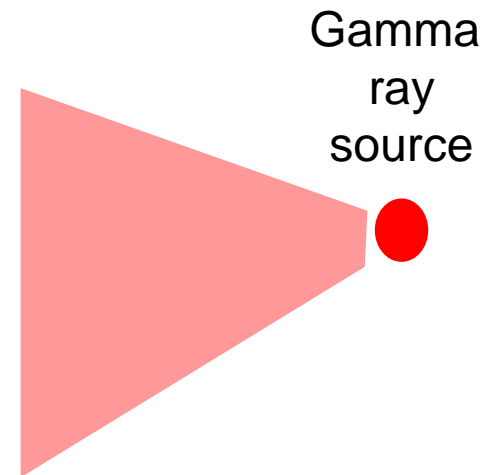
**Collaboration with UC Davis:  
Junwei Du and Simon Cherry**



1.5 x 1.5 cm<sup>2</sup>  
4 readout  
channels only



LYSO array  
30 x 30 array of 0.445 x 0.445 x 20 mm<sup>3</sup>  
Pitch size is 0.5 mm.



# Are we able to identify all crystals?

